

Si4532DY*

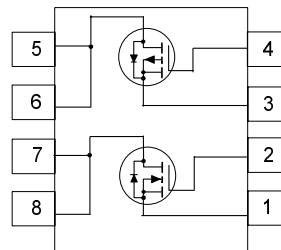
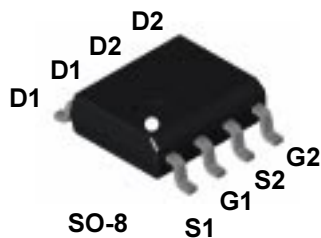
Dual N- and P-Channel Enhancement Mode Field Effect Transistor

General Description

These dual N- and P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- N-Channel 3.9A, 30V. $R_{DS(ON)} = 0.065\Omega @V_{GS} = 10V$
 $R_{DS(ON)} = 0.095\Omega @V_{GS} = 4.5V.$
- P-Channel -3.5A, -30V. $R_{DS(ON)} = 0.085\Omega @V_{GS} = -10V$
 $R_{DS(ON)} = 0.190\Omega @V_{GS} = -4.5V.$
- High density cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability in a widely used surface mount package.
- Dual (N & P-Channel) MOSFET in surface mount package.



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	N-Channel	P-Channel	Units
V _{DSS}	Drain-Source Voltage	30	-30	V
V _{GSS}	Gate-Source Voltage	20	-20	V
I _D	Drain Current - Continuous (Note 1a)	3.9	-3.5	A
	- Pulsed	20	-20	
P _D	Power Dissipation for Dual Operation	2		W
	Power Dissipation for Single Operation (Note 1a)	1.6		
	(Note 1b)	1		
	(Note 1c)	0.9		
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150		°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
4532	Si4532DY	13"	12mm	2500 units

* Die and manufacturing source subject to change without prior notification.

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	N-Ch	30			V
		$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	P-Ch	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1	μA
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	All			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	All			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	N-Ch	1		3	V
		$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	P-Ch	-1		-3	V
$R_{DS(on)}$	Static Drain-Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 3.9\text{ A}$	N-Ch		0.053	0.065	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 3.1\text{ A}$			0.081	0.095	
		$V_{GS} = -10\text{ V}, I_D = -2.5\text{ A}$	P-Ch		0.06	0.085	
		$V_{GS} = -4.5\text{ V}, I_D = -1.8\text{ A}$			0.095	0.19	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	N-Ch	15			A
		$V_{GS} = -10\text{ V}, V_{DS} = -5\text{ V}$	P-Ch	-15			
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 3.9\text{ A}$	N-Ch		7		S
		$V_{DS} = -15\text{ V}, I_D = -2.5\text{ A}$	P-Ch		5		

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	N-Ch		235		pF	
			P-Ch		420			
C_{oss}	Input Capacitance		$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	N-Ch		150		pF
				P-Ch		140		
C_{riss}	Reverse Transfer Capacitance			N-Ch		49		pF
				P-Ch		60		

Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Switching Characteristics (Note 2)

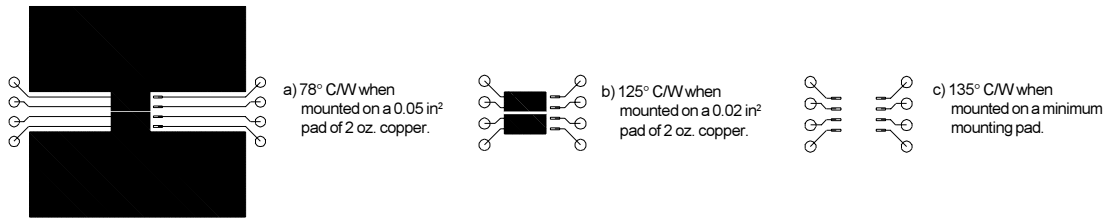
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{ V}$, $I_D = 1\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\ \Omega$	N-Ch		7	13	ns
			P-Ch		9	18	
t_r	Turn-On Rise Time		N-Ch		18	29	ns
			P-Ch		8	16	
$t_{d(off)}$	Turn-Off Delay Time	$V_{DD} = -10\text{ V}$, $I_D = -2.5\text{ A}$, $V_{GS} = -10\text{ V}$, $R_{GEN} = 6\ \Omega$	N-Ch		15	27	ns
			P-Ch		18	29	
t_f	Turn-Off Fall Time		N-Ch		0.8	8	ns
			P-Ch		6	12	
t_{rr}	Drain-Source Reverse Recovery Time	$I_F = 1.7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $I_F = -1.7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch			80	nS
			P-Ch			80	
Q_g	Total Gate Charge	$V_{DS} = 10\text{ V}$, $I_D = 3.9\text{ A}$, $V_{GS} = 10\text{ V}$	N-Ch		3.7	15	nC
			P-Ch		5	15	
Q_{gs}	Gate-Source Charge	$V_{DS} = -10\text{ V}$, $I_D = -2.5\text{ A}$, $V_{GS} = -10\text{ V}$	N-Ch		0.9		nC
			P-Ch		1.7		
Q_{gd}	Gate-Drain Charge		N-Ch		1.9		nC
			P-Ch		1.8		

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current		N-Ch			1.7	A
			P-Ch			-1.7	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 1.7\text{ A}$ (Note 2)	N-Ch		0.75	1.2	V
			P-Ch		-0.75	-1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

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